

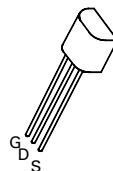
N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVN2110C

ISSUE 2 – MARCH 94

FEATURES

- * 100 Volt V_{DS}
- * $R_{DS(on)} = 4\Omega$



E-Line
TO92 Compatible

REFER TO ZVN2110A FOR GRAPHS

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	100	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	320	mA
Pulsed Drain Current	I_{DM}	6	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	700	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	100		V	$I_D=1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	$I_D=1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		1 100	μA μA	$V_{DS}=100V, V_{GS}=0$ $V_{DS}=80V, V_{GS}=0V, T=125^{\circ}C(2)$
On-State Drain Current(1)	$I_{D(on)}$	1.5		A	$V_{DS}=25V, V_{GS}=10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		4	Ω	$V_{GS}=10V, I_D=1A$
Forward Transconductance (1)(2)	g_{fs}	250		mS	$V_{DS}=25V, I_D=1A$
Input Capacitance (2)	C_{iss}		75	pF	$V_{DS}=25V, V_{GS}=0V, f=1MHz$
Common Source Output Capacitance (2)	C_{oss}		25	pF	
Reverse Transfer Capacitance (2)	C_{rss}		8	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		7	ns	$V_{DD}=25V, I_D=1A$
Rise Time (2)(3)	t_r		8	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		13	ns	
Fall Time (2)(3)	t_f		13	ns	

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$

(2) Sample test.